Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	2	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
Dynamic	characteristics					,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	2000	-	V/µs
dI _{com} /dt	rate of change of commutating curren	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit	30	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N 1
2	T2	main terminal 2		T2—T1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA312B-800B	TO263	BTA312B-800B,118	Reel	800	TO263E	26-May-2017

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 100 °C; Fig. 1; Fig. 2; Fig. 3	-	12	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	-	100	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	110	Α
l ² t	I ² t for fusing	t _P = 10 ms; SIN	-	50	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 120 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

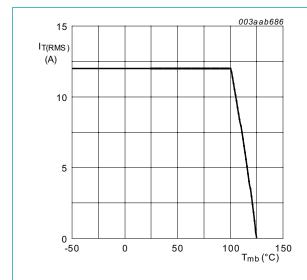
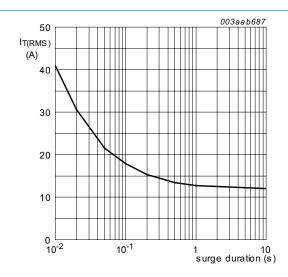
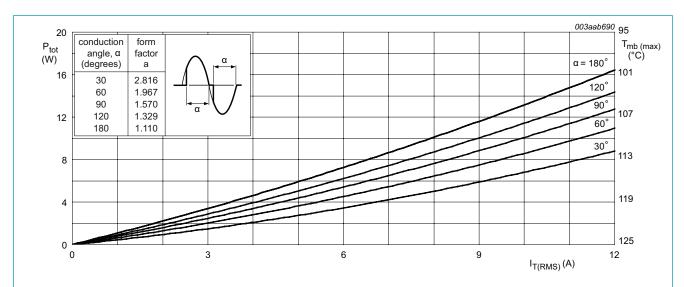


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



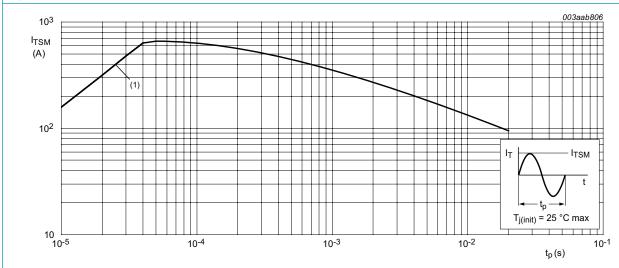
f = 50 Hz; T_{mb} = 100 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)}/I_{T(AV)}$

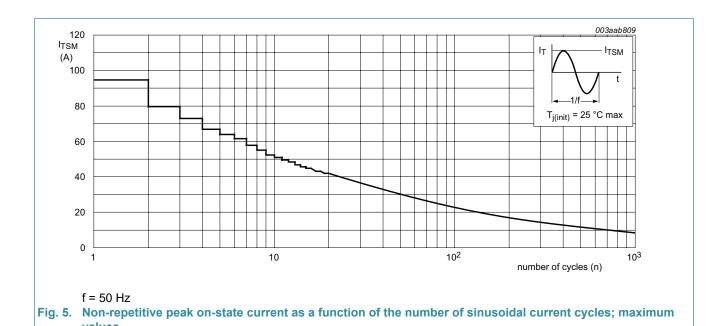
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$

(1) dl_T/dt limit

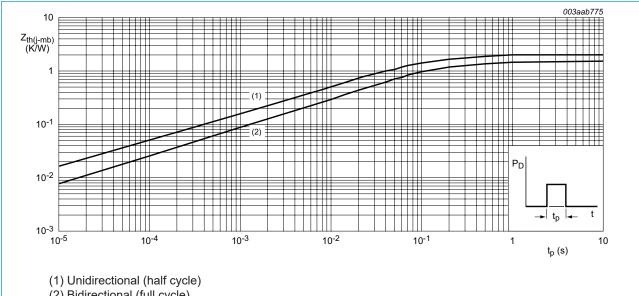
Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
uiti-iiib)	thermal resistance	full cycle; Fig 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



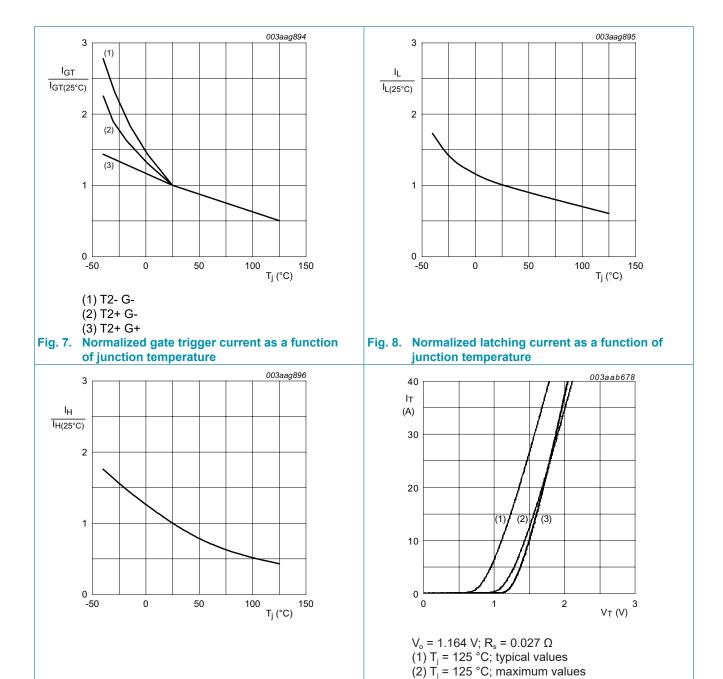
(2) Bidirectional (full cycle)

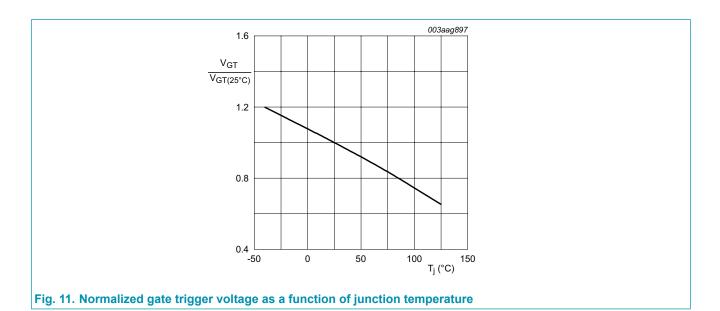
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	50	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2+ G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A;} T_j = 25 \text{ °C;}$ Fig. 11	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	2000	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V; } T_j = 125 \text{ °C; } I_{T(RMS)} = 12 \text{ A;}$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s; (snubberless condition); gate open circuit}$	30	-	-	A/ms





10. Package outline

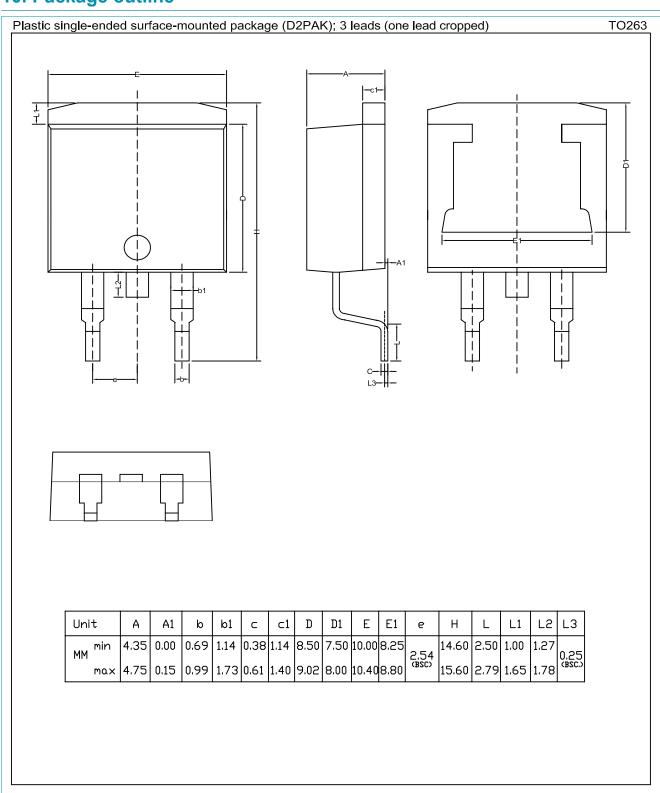


Fig. 12. Package outline TO263

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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